NEC

SILICON TRANSISTOR ARRAY

μPA1434

NPN SILICON POWER TRANSISTOR ARRAY
LOW SPEED SWITCHING USE
INDUSTRIAL USE

DESCRIPTION

The μPA1434 is NPN silicon epitaxial Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- Easy mount by 0.1 inch of terminal interval.
- High h_{FE}. Low $V_{CE(sat)}$.
  h_{FE} = 800 to 3200 (at I_C = 0.5 A)
  $V_{CE(sat)}$ = 0.5 V MAX. (at I_C = 2 A)

ORDERING INFORMATION

Part Number	Package	Quality Grade
μPA1434H	10 Pin SIP	Standard

Please refer to "Quality grade on NEC Semiconductor Device" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

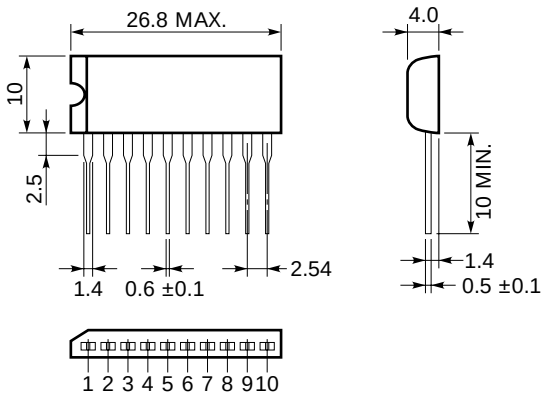
ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7	V
Collector Current (DC)	$I_{C(DC)}$	3	A/unit
Collector Current (pulse)	$I_{C(pulse)}$*	6	A/unit
Base Current (DC)	$I_{B(DC)}$	0.6	A/unit
Total Power Dissipation (T_a = 25 °C)	P_{T1}**	3.5	W
Total Power Dissipation (T_c = 25 °C)	P_{T2}**	28	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C

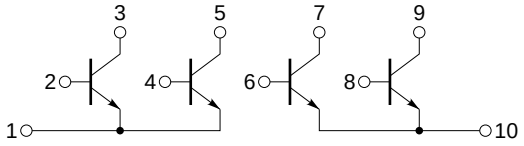
* PW ≤ 300 μs, Duty Cycle ≤ 10 %

** 4 Circuits

PACKAGE DIMENSION
(in millimeters)



CONNECTION DIAGRAM



PIN NO.

2, 4, 6, 8: Base (B)
3, 5, 7, 9: Collector (C)
1, 10: Emitter (E)

The information in this document is subject to change without notice.

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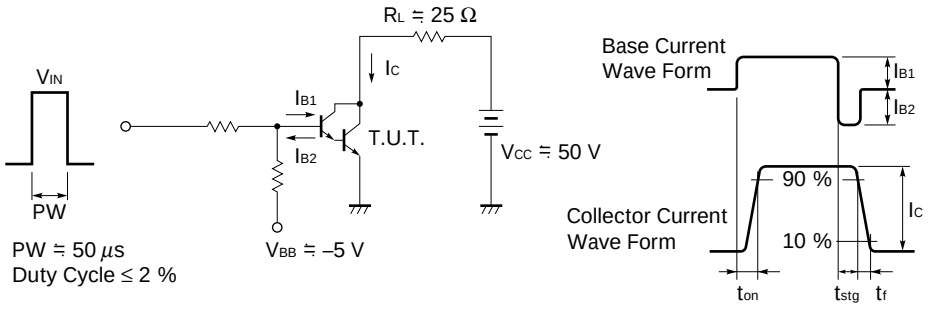
ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Leakage Current	I_{CBO}			10	μA	V_{CB} = 60 V, I_E = 0
Emitter Leakage Current	I_{EBO}			10	μA	V_{EB} = 5 V, I_C = 0
DC Current Gain	h_{FE1} *	800		3200	—	V_{CE} = 5 V, I_C = 0.5 A
DC Current Gain	h_{FE2} *	500			—	V_{CE} = 5 V, I_C = 3 A
Collector Saturation Voltage	$V_{CE(sat)}$ *			0.5	V	I_C = 2 A, I_B = 20 mA
Base Saturation Voltage	$V_{BE(sat)}$ *			1.2	V	I_C = 2 A, I_B = 20 mA
Turn On Time	t_{on}		1		μs	I_C = 2 A I_{B1} = $-I_{B2}$ = 10 mA V_{CC} ≒ 50 V, R_L ≒ 25 Ω See test circuit
Storage Time	t_{stg}		3		μs	
Fall Time	t_f		1.5		μs	

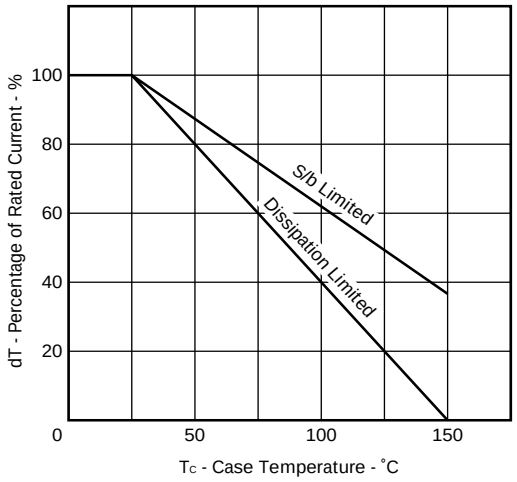
* PW ≤ 350 μs, Duty Cycle ≤ 2 % /pulsed

SWITCHING TIME TEST CIRCUIT

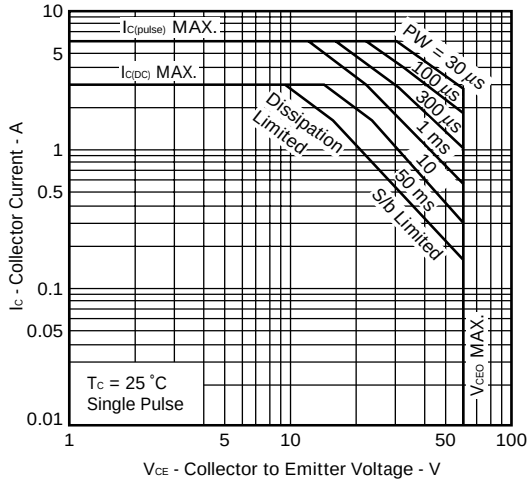


TYPICAL CHARACTERISTICS (T_a = 25 °C)

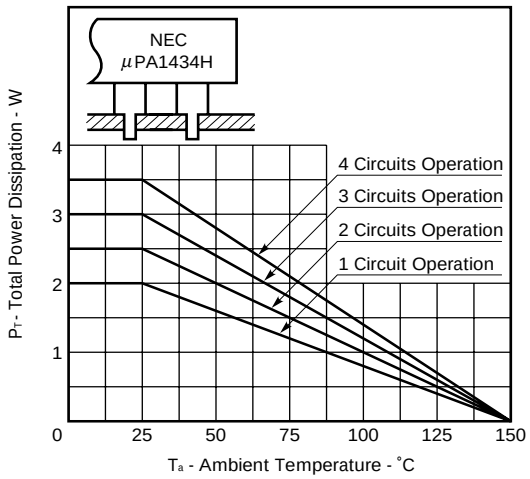
DERATING CURVE OF SAFE OPERATING AREA



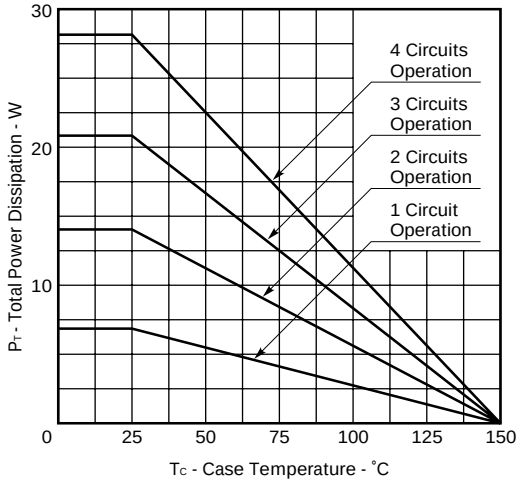
SAFE OPERATING AREA



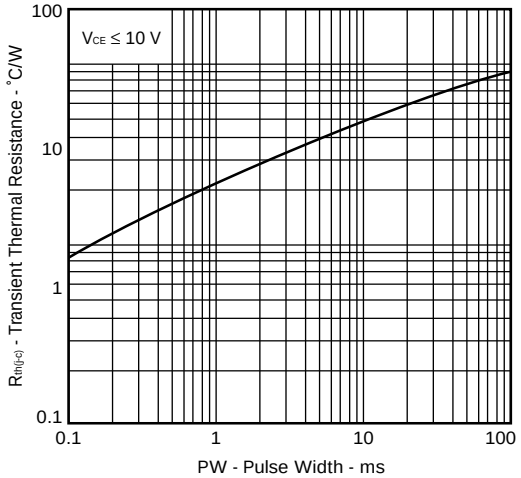
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



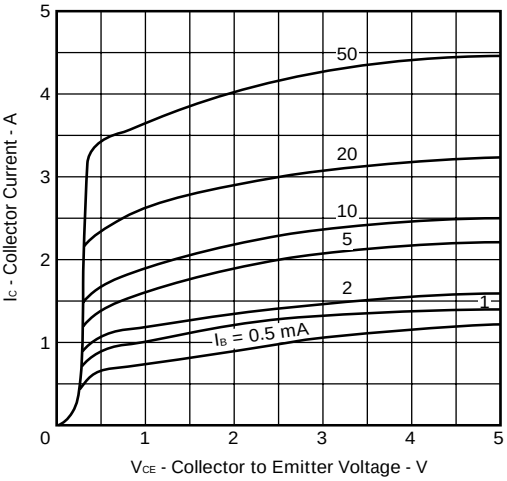
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



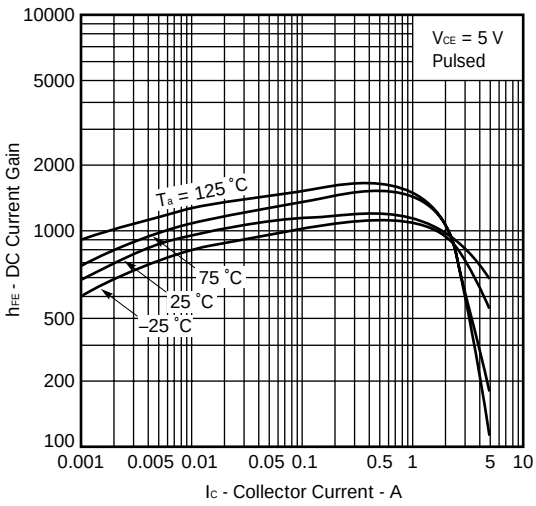
TRANSIENT THERMAL RESISTANCE



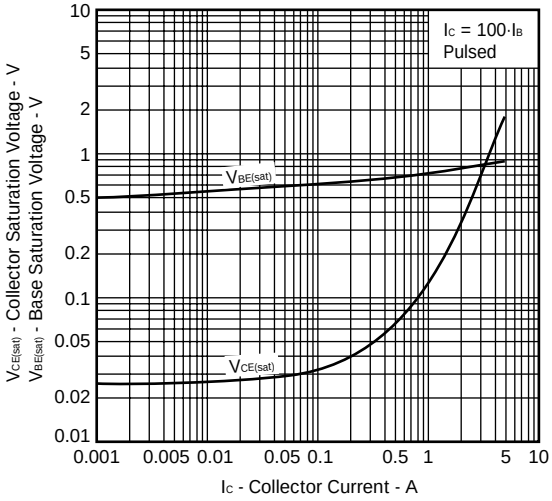
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE vs.COLLECTOR CURRENT



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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